# **Xyce**<sup>™</sup> Parallel Electronic Simulator Release Notes

Release 5.2.1

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## **Xyce<sup>™</sup> Parallel Electronic Simulator Release Notes**Release 5.2.1

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### Scope/Product Definition

The **Xyce** Parallel Electronic Simulator has been written to support, in a rigorous manner, the simulation needs of the Sandia National Laboratories electrical designers. Specific requirements include, among others, the ability to solve extremely large circuit problems by supporting large-scale parallel computing platforms, improved numerical performance and object-oriented code design and implementation.

The **Xyce** release notes describe:

- Hardware and software requirements
- New features and enhancements
- Any defects fixed since the last release
- Current known defects and defect workarounds

For up-to-date information not available at the time these notes were produced, please visit the **Xyce** web page at <a href="http://xyce.sandia.gov/">http://xyce.sandia.gov/</a>.

#### Hardware/Software

This section gives basic information on supported platforms and hardware and software requirements for running **Xyce** 5.2.1.

#### Supported Platforms (Certified Support)

**Xyce** 5.2.1 currently supports any of the following operating system (all versions imply the earliest supported – **Xyce** generally works on later versions as well) platforms. These platforms are supported in the sense that they have been subject to certification testing for the **Xyce** version 5.2.1 release.

- Red Hat Enterprise Linux<sup>®</sup> 5, x86 and x86-64 (serial and parallel)
- Microsoft Windows 7<sup>®</sup>, x86 (serial)
- Apple<sup>®</sup> OS X, x86-64 (serial and parallel)
- TLCC (serial and parallel)
- Red Sky (serial and parallel)

#### Build Supported Platforms (not Certified)

The platforms listed in this section are "not supported" in the sense that they are not subject to nightly regression testing, and they also were not subject to certification testing for the **Xyce** version 5.2.1 release.

- Xyce directly coupled to the Dakota optimization and uncertainty quantification library for Apple OS X and Linux platforms.
- FreeBSD 7.x on Intel x86 architectures (serial and parallel)

Please contact the Xyce development team for platform and configuration availability.

#### Hardware Requirements

The following are *estimated* hardware requirements for running **Xyce**:

- 128MB memory memory minimum memory requirements increase with circuit size
- 128MB disk space required for installation (does not include space needed for output files)

#### Software Requirements

Several libraries are required to run **Xyce** or build **Xyce** from source on a platform. Serial versions of the static **Xyce** binary have no run-time software requirements. However, parallel versions require the following software at run time:

- Open MPI (http://www.open-mpi.org/) (version 1.4 or higher)
- Intel (http://www.intel.com/) MKL (version 10.2) and Compilers (version 11.1)
- TLCC and Red Sky users can load the **xyce** module to properly set the environment

Several libraries (all freely available from Sandia National Laboratories or other sites) are always required when building **Xyce** from source. These are:

- Trilinos Solver Library version 10.2 (Sandia, http://trilinos.sandia.gov). This is a suite of libraries including Amesos, AztecOO, Belos, Teuchos, Epetra, EpetraExt, Ifpack, NOX, LOCA, Sacado, Zoltan.
- SuperLU (libsuperlu.a) (http://crd.lbl.gov/ xiaoye/SuperLU/)
- UMFPACK version 4.1 and AMD version 1.0 (libumfpack.a, libamd.a) (http://www.cise.ufl.edu/research/sparse/umfpack/)
- LAPACK
- BLAS

For parallel builds, the following libraries are additionally required:

- MPI (http://www.open-mpi.org) library for message passing (version 1.4 or higher). The version used to build Xyce must be the same that is used for building Trilinos.
- ParMETIS (http://glaros.dtc.umn.edu/gkhome/views/metis) library for graph partitioning (version 3.1 or higher). The MPI compiler used to compile ParMETIS must be the same that is used for Trilinos and Xyce.

## **Xyce** Release 5.2.1 Documentation

The following **Xyce** documentation is available at the **Xyce** internal website in pdf form.

- **Xyce** Users' Guide, Version 5.2.1
- Xyce Reference Guide, Version 5.2.1

- Xyce Release Notes, Version 5.2.1
- **Xyce** Theory Document
- EKV MOSFET version 3.0.1 model documentation.
- Xyce Test Plan

#### New Features and Enhancements

Highlights for **Xyce** Release 5.2.1 include:

- Improved formulation for the nonlinear mutual inductor device including the ability to output *B-H* loops. See the special notes section under the nonlinear mutual inductor device in the reference guide for details.
- New time integration options: newlte and newbpstepping.
- New support for maxord and minord in variable-order trapezoid (Adams method) algorithm.

For details of each of these new features, see the **Xyce** Users' Guide, and the **Xyce** Reference Guide. Also, a more complete listing of new features and improvements are given in the following sections.

#### **Device Support**

Table 1 contains a complete list of devices for **Xyce** Release 5.2.1

Device	Comments
Capacitor	Age-aware, semiconductor
Inductor	Nonlinear mutual inductor (see below)
Nonlinear Mutual Inductor	Sandia Core model (not fully PSpice compatible)
	Stability improvements
Resistor (Level 1)	Semiconductor
Resistor (Level 2)	Thermal Resistor
Diode (Level 1)	
Diode (Level 2)	Addition of PSPICE enhancements
Diode (Level 3)	Prompt and delayed photocurrent radiation model
Diode (Level 4)	Generic photocurrent source model
Independent Voltage Source (VSRC)	

Device	Comments
Independent Current Source (ISRC)	
Voltage Controlled Voltage Source	
(VCVS)	
Voltage Controlled Current Source	
(VCCS)	
Current Controlled Voltage Source	
(CCVS)	
Current Controlled Current Source	
(CCCS)	
Nonlinear Dependent Source (B	
Source) Bipolar Junction Transistor (BJT)	
(Level 1)	
Bipolar Junction Transistor (BJT)	
(Level 2)	Prompt photocurrent radiation model
Bipolar Junction Transistor (BJT)	Neutron-effects model
(Level 3)	Neutron-effects model
Bipolar Junction Transistor (BJT)	Prompt photocurrent radiation model (same as level 2)
(Level 4)	Trompt photocarront radiation model (came as lovel 2)
Bipolar Junction Transistor (BJT)	Deveney-Wrobel Neutron model, with photocurrent
(Level 5)	
Bipolar Junction Transistor (BJT)	Physics-based (QASPR) Neutron model, with
(Level 6)	photocurrent
Bipolar Junction Transistor (BJT)	Vertical Bipolar Intercompany (VBIC) model Updated!
(Level 10) Heterjunction Bipolar Transistor	
, ,	Prompt neutron radiation model model New!
(HBT) (Level 222)  Junction Field Effect Transistor	
(JFET) (Level 1)	SPICE-compatible JFET model
Junction Field Effect Transistor	Shooklay IEEE madal
(JFET) (Level 2)	Shockley JFET model
MESFET	
MOSFET (Level 1)	
MOSFET (Level 2)	Spice level 2 MOSFET
MOSFET (Level 3)	
MOSFET (Level 6)	Spice level 6 MOSFET
MOSFET (Level 9)	BSIM3 model with initial condition support
MOSFET (Level 10)	BSIM SOI model with initial condition support
MOSFET (Level 11)	BSIM SOI model with Transient Photocurrent
,	

Device	Comments				
MOSFET (Level 12)	BSIM SOI model with Transient Photocurrent				
MOSFET (Level 14)	BSIM4 model				
MOSFET (Level 18)	VDMOS general model				
MOSFET (Level 19)	VDMOS total dose radiation model				
MOSFET (Level 20)	VDMOS photocurrent model				
MOSFET (Level 21)	Level 1 with photocurrent				
MOSFET (Level 23)	Level 3 with photocurrent				
MOSFET (Level 103)	PSP model New!				
MOSFET (Level 301)	EKV model New!				
Transmission Line	Lossless				
Controlled Switch (S,W)	Voltage or current controlled				
(VSWITCH/ISWITCH)					
Generic Switch (SW)	Controlled by an expression				
PDE Devices (Level 1)	one-dimensional				
PDE Devices (Level 2)	two-dimensional				
PDE Devices (Level 3)	one-dimensional, with neutron damage physics New!				
Digital (Level 1)	Behavioral Digital				
EXT (Level 1)	External device, used for code coupling and				
	power-node parasitics simulations				
OP AMP (Level 1)	Ideal operational amplifier				
ACC	Accelerated mass device, used for simulation of				
	electromechanical and magnetically-driven machines				
NEUTRON (Level 1)	Stand-alone neutron device model				
ROM (Level 1)	Reduced-order model device for linear (RLC) circuits				

Table 1: Devices Supported by Xyce

#### **New Devices**

- New compact neutron model for heterojunction bipolar transistors, which is based on an empirical formula for defect-induced recombination current. This is the level=222 BJT model.
- New compact neutron model for Silicon, which uses a numerical, instead of analytic, carrier model. This is the level=3 pde model.
- PSP MOSFET model. This is an advanced surface-potential-based compact model for MOSFETs, developed at Pennsylvania State University and Philips Research Laboratory.

- EKV MOSFET model. This model is a scalable and compact MOSFET model developed for use in the simulation of circuits using submicron CMOS technologies.
- PNP VBIC model. The industry-standard VBIC model for Heterojunction Bipolar Transistors (HBTs) has been extended in this version of **Xyce** to support PNP devices as well as NPN.

## Defects of Release 5.1 Fixed in this Release

Defect	Description					
	Devices that are generated via reduced-order modeling					
bug 211 : ROM Device improvements	(ROM) methods and, subsequently, integrated into a circuit can generate large dense blocks in the Jacobian matrix. These blocks can adversely affect the performance of the linear solver, which assumes a sparse matrix structure. An alternative formulation is now available for ROM devices that avoids generating this dense block, by using a two-level solution method. This can be enabled via setting USE_PORT_DESCRIPTION=1 in the ROM device line.					
1 1000 TI	In versions of <b>Xyce</b> prior to 5.2.1 the thermal resistor					
bug 1832 : Thermal resistor	(LEVEL=2) had a bug that resulted in improper computation if instance parameters such as L or A were					
correctly works with global parameters	specified as expressions involving global parameters (i.e. those defined by a .global_param statement). This has been fixed.					
bug 1833 : Flexibility in Neutron						
Model Specification						
	Some circuits containing nonlinear mutual inductor					
<b>bug 1829</b> : Optimized version of Xyce fails in .STEP analysis.	devices would fail when used in .STEP analysis. The root cause for this was a numeric instability in the formulation of the nonlinear mutual inductor model. This device has been improved, however, the previous formulation can be largely recovered by including factorms=1 in the device's .model line. The new formulation for the nonlinear mutual inductor is faster and more stable in most circuits and it appears that the best time integration options to use with it are .options timeint method=6 newlte=1 newbpstepping=1 nlnearconv=0 reltol=1.0e-3.					

Table 2: Fixed Defects.

## Known Defects and Workarounds

Defect	Description
	The diagnostic code used by the <b>Xyce</b> setup that
Connectivity checking is broken for devices with more than 10 leads [SON Bug 37]	checks circuit topology for basic errors such as a node having no DC path to ground or a node being connected to only one device has a bug in it that causes the code to emit a cryptic error message, "Internal: lead index not found" after which the code will exit. This error has so far only been seen when a user has attempted to connect a large number of inductors together using multiple mutual inductor lines. The maximum number of non-ground leads that can be used without confusing this piece of code is 10. If you see the error message "Internal: lead index not found." and you have such a large mutual inductor, this bug is the source of the problem.  **Workaround:** Disable connectivity checking by adding the line  **OPTIONS TOPOLOGY CHECK_CONNECTIVITY=0**  to your netlist. This will disable the check for the basic errors such as floating nodes and improperly connected devices, but will allow the netlist to run with a highly-connected mutual inductor.
.DC sweep output.	.DC sweep calculation does not automatically output sweep results.  Workaround: Use .PRINT statement to output sweep variable results.
BJT Current Crowding	"Timestep too small" failures can result when IRB nonzero with level 2 and level 4 BJT Workaround: If such failure observed, disable current crowding effect by setting IRB to zero in all BJT models. Please feed back such circuits to the <b>Xyce</b> development team so that this bug can be characterized and eliminated.
Microsoft Windows installation restrictions	Users with insufficient privileges (i.e.  Limited Account) are not permitted to install <b>Xyce</b> into folders on the System Drive (usually C:).  Workaround: First, manually create the desired folder on the System Drive. It is then possible to install <b>Xyce</b> into this folder by following the standard Setup procedure.

Defect	Description				
	Netlists created with programs like Microsoft Word and				
Incompatible proprietary file formats.	Microsoft Wordpad will not run in <b>Xyce</b> . <b>Xyce</b> does not recognize proprietary file formats. <i>Workaround:</i> It is best not to use such programs to create netlists, unless netlists are saved as *.txt files. If you must use a Microsoft editor, it is better to use Microsoft Notepad. In general, the best solution is to use a Unix-style editor, such as Vi, Gvim, or Emacs.				
	There is one case for a customer's parallel run of a				
One known instance of restart results not matching original run results.	large digital circuit of BSIM3's where the restart output does not match the original results for the same time range.  Workaround: The only choice for now is to check the restart results against the baseline results for some block if the run results have a very tight tolerance for success. It is suggested to overlap the original run time with the restart time allowing comparison.				
	The nonlinear dependent source ("B-source") allows				
Infinite-slope transitions in B-sources causes "time step too small" errors [bug 772]	the user to specify expressions that could have infinite-slope transitions, such as				
	Bcrtl OUTA 0 V={ IF( (V(IN) > 3.5), 5, 0 ) }				
	This can lead to "timestep too small" errors when <b>Xyce</b> reaches the transition point. Infinite-slope transitions in expressions dependent only on the time variable are a special case, because <b>Xyce</b> can detect that they are going to happen in the future and set a "breakpoint" to capture them. Infinite-slope transitions depending on other solution variables cannot be predicted in advance, and cause the time integrator to scale back the timestep repeatedly in an attempt to capture the feature until the timestep is too small to continue. <i>Workaround:</i> Do not use step-function or other infinite-slope transitions dependent on variables other than time. Smooth the transition so that it is more easily integrated through.				

Defect	Description					
	If <b>Xyce</b> is run in parallel on a netlist that is so small that					
Epetraext uses bad address in parallel, causing <b>Xyce</b> core dump [bug 1072]	all devices are assigned to the same processor, <b>Xyce</b> can core dump when the processor with no work attempts to access invalid memory. <i>Workaround:</i> It is best not to try to run <b>Xyce</b> on very small problems in parallel, as this capability is intended for and optimzed for very large problems; small problems should be run in serial. If trying to run medium-sized problems in parallel and these core dumps are observed, try running with Zoltan partitioning and singleton removal turned off:  .OPTIONS LINSOL TR_partition=0  + TR_singleton_filter=0					
	Workaround: Improved speed and accuracy in circuits					
Small circuits with nonlinear mutual inductor devices may produce different results when run in parallel. [bug 1838]	using the nonlinear mutual inductor device were found when the magnetic saturation parameter $Ms$ was no longer factored out of the magnetic moment variable, $M$ as it had been been in prior version of <b>Xyce</b> However, this same change may make circuits that are run in parallel with serial solvers produce different results. A way to mitigate this difference is to return to the old factorization of $Ms$ by setting factorms=1 in the .model CORE line for the nonlinear mutual inductor element.					

Table 3: Known Defects and Workarounds.

## Incompatibilities With Other Circuit Simulators

Issue	Comment					
AC Analysis not supported	Xyce does not currently support AC analysis.					
	A .OP netlist will run in Xyce, but will not produce the					
.OP is not complete	extra output normally associated with the .0P statement.					
	A requested pulsed source rise/fall time of zero really is					
Pulsed source rise time of zero.	zero in Xyce. In other simulators, requesting a zero rise/fall time causes them to use the printing interval found on the .TRAN line.					
	Not the same as PSpice. This is a Sandia developed					
Mutual Inductor Model.	model but is compatible with Cadence PSpice parameter set.					
	Output variables have to be specified as V(node) or					
.PRINT line shorthand.	I(source). Specifying the node alone will not work. Also, specifying V(*) or I(*) (to get all voltages or currents) will not work.					
BSIM3 level.	In <b>Xyce</b> the BSIM3 level=9. Other simulators have					
	different levels for the BSIM3.					
BSIM SOI v3.2 level.	In <b>Xyce</b> the BSIM SOI (v3.2) level=10. Other					
	simulators have different levels for the BSIM SOI.					
	Currently, circuit nodes and devices MUST have					
Node names vs. device names.	different names in <b>Xyce</b> . Some simulators can handle a device and a node with the same name, but <b>Xyce</b> cannot.					
Interactive mode.	<b>Xyce</b> does not have an interactive mode.					
	These are not currently supported within <b>Xyce</b> .					
ChileSPICE-specific "operating point voltage sources."	However <b>Xyce</b> does support "IC= <value>" statements for capacitors, inductors, and the two BSIM devices which will automatically set these voltage drops at the beginning of a transient simulation.</value>					
Syntax for .STEP is different.	The manner of specifying a model parameter to be swept is slightly different. See the Users' and Reference Guides for details.					

Table 4: Incompatibilities with other circuit simulators.

## Important Changes to **Xyce** Usage Since the Release 5.1.

Table 5 lists some usage changes for **Xyce**.

Issue		Comment					
	T 11 E O1	 	161 .1				

Table 5: Changes to netlist specification since the last release.

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**Xyce**'s expression library is based on that inside Spice 3F5 developed by the EECS Department at the University of California.

The EKV3 MOSFET model was developed by the EKV Team of the Electronics Laboratory-TUC of the Technical University of Crete.

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